NSN 5962-01-351-4990

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-351-4990

Overall Length:

1.060 inches

Overall Height:

0.400 inches

Body Length:

1.060 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

Between 0.130 inches and 0.185 inches

Maximum Power Dissipation Rating:

2.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Satellite communications terminal an/usc-3 (v) 1

Features Provided:

Programmed and monolithic and w/clock and bidirectional

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

185.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

And-or invert gate array

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

45.00 nanoseconds propagation delay time, high to low level output and 45.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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